

DMN5/L06VK/L06VAK/010VAK

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 2)
- Halogen and Antimony Free
- "Green" Device (Note 3)
- . ESD Protected up to 2kV

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.006 grams (approximate)

SOT-563





TOP VIEW





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$	V_{DGR}	50	V	
Gate-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 1)	Continuous Pulsed	I _D I _{DM}	280 1.5	mA A

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P _D	250	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

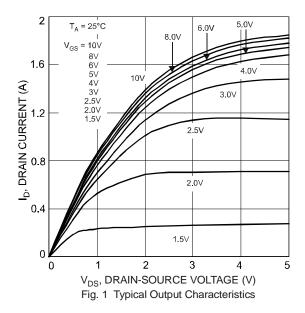
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

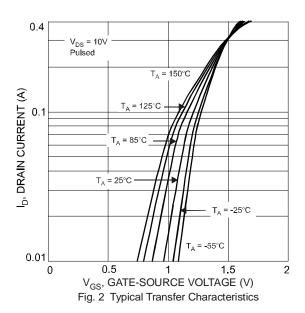


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C	I _{DSS}	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
					1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage		IGSS	_	_	500	nА	$V_{GS} = \pm 10V$, $V_{DS} = 0V$
					50	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		$V_{GS(th)}$	0.49		1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			_		3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance		R _{DS (ON)}	_	_	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
			_		2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current		I _{D(ON)}	0.5	1.4		Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage		V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_		50	pF	\/ OF\/\\
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	_	5.0	pF	T = T.UIVII IZ

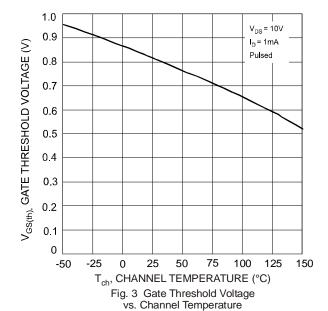
Notes: 4. Short duration pulse test used to minimize self-heating effect.

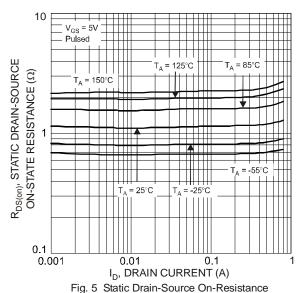


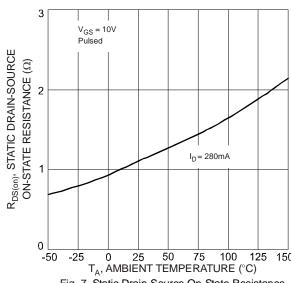












vs. Drain Current

Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

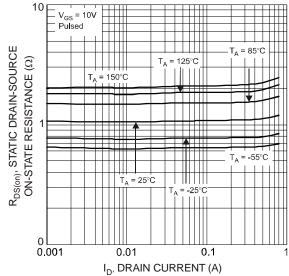


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

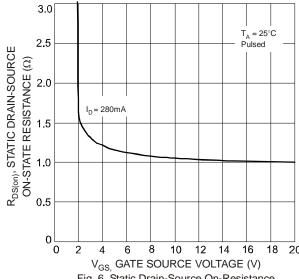


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

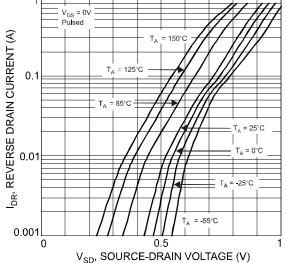
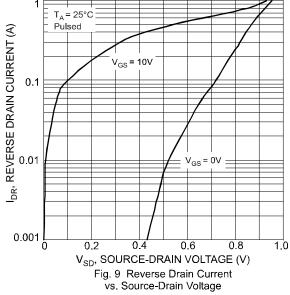
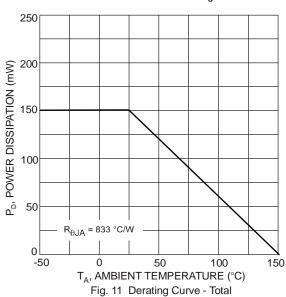
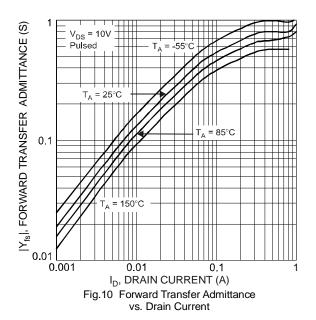


Fig. 8 Reverse Drain Current
vs. Source-Drain Voltage









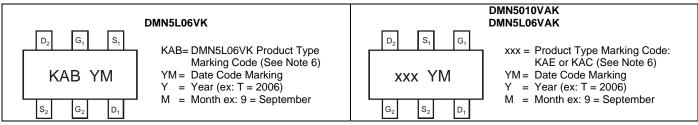


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN5L06VK-7	SOT-563	3000/Tape & Reel
DMN5L06VAK-7	SOT-563	3000/Tape & Reel
DMN5010VAK-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information (Note 6)

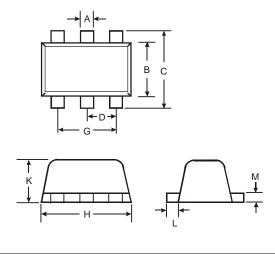


Notes: 6. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Date Code Key

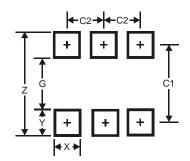
Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	T		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
O	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Η	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
M	0.10	0.18	0.11			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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